

FIG. 1

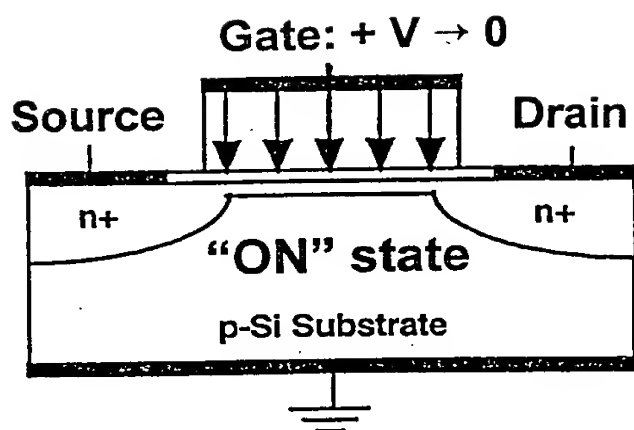


FIG. 2

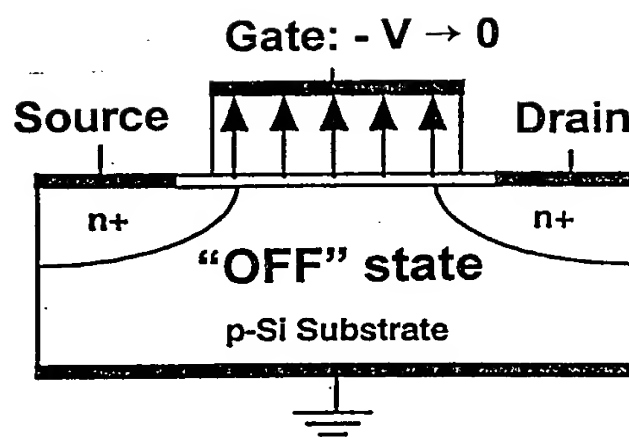


FIG. 3

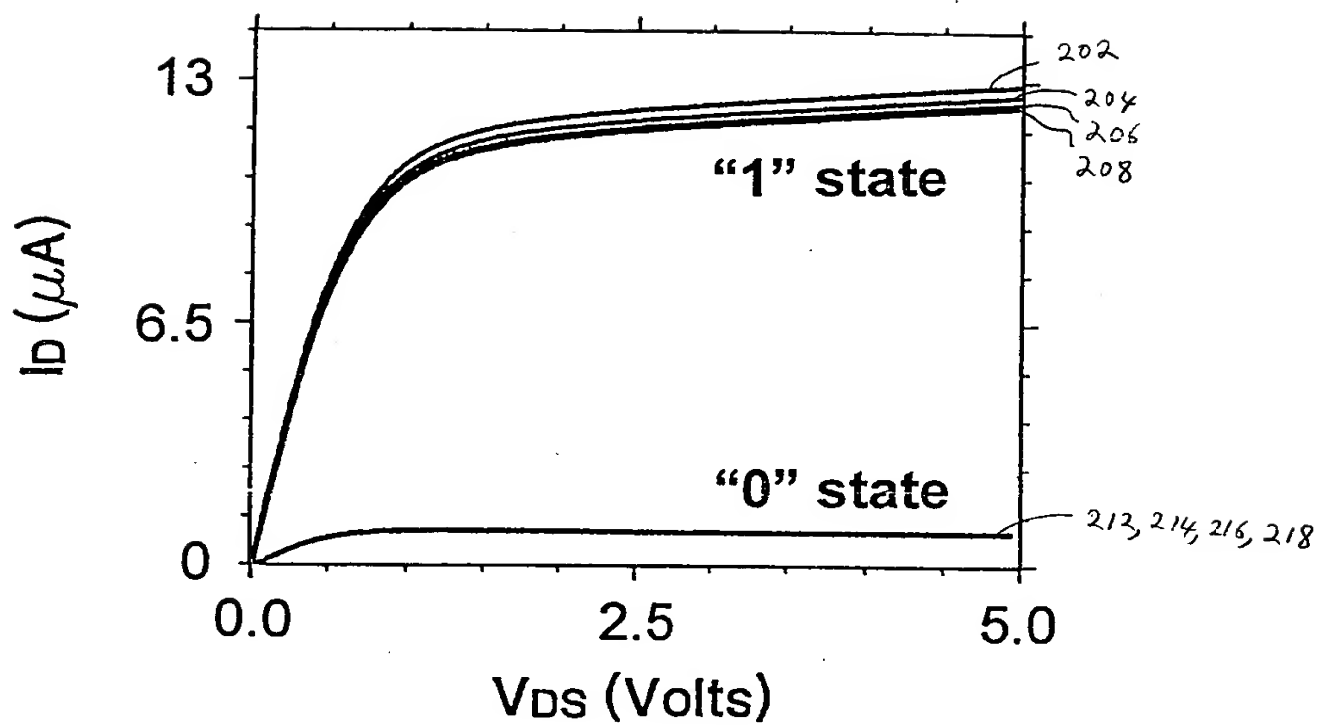


FIG. 4

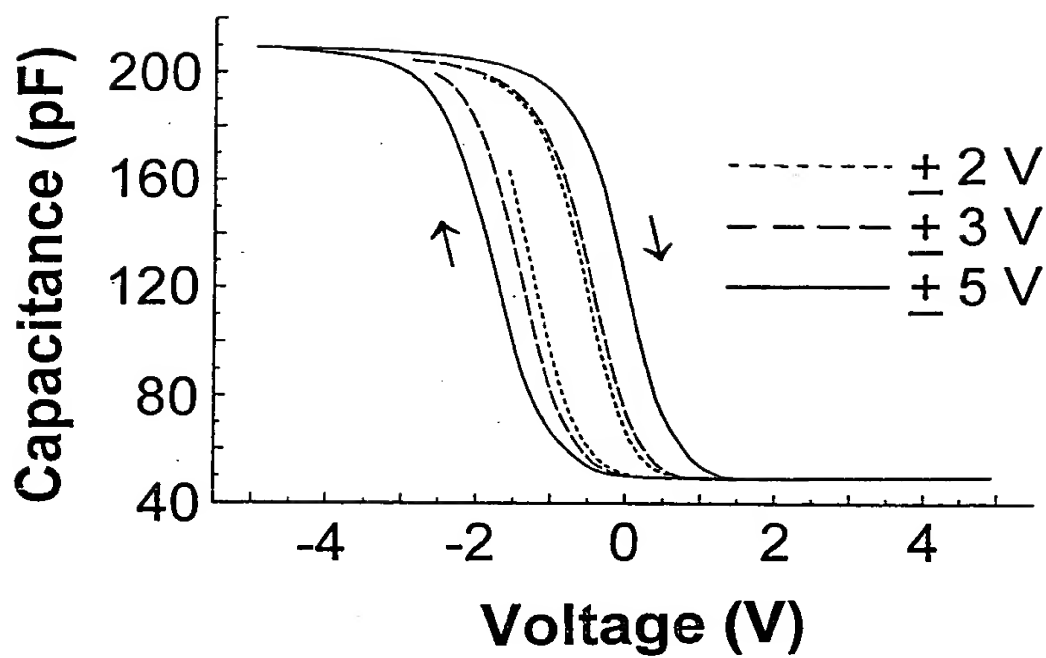


FIG. 5

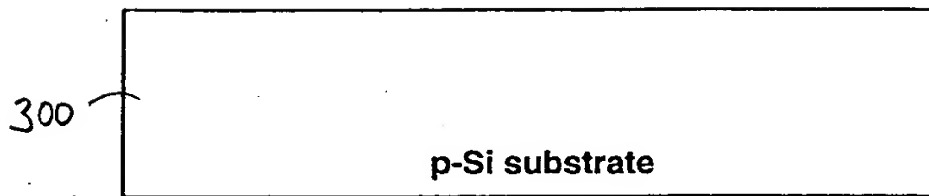


FIG. 6

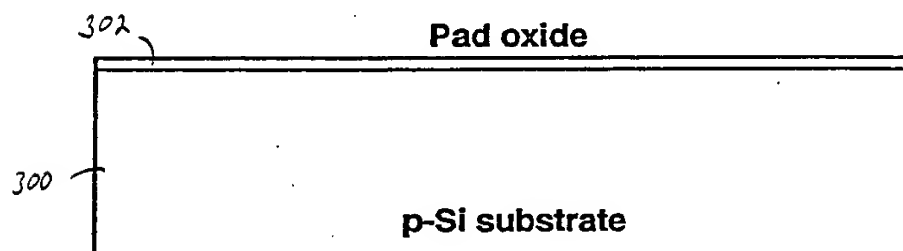


FIG. 7

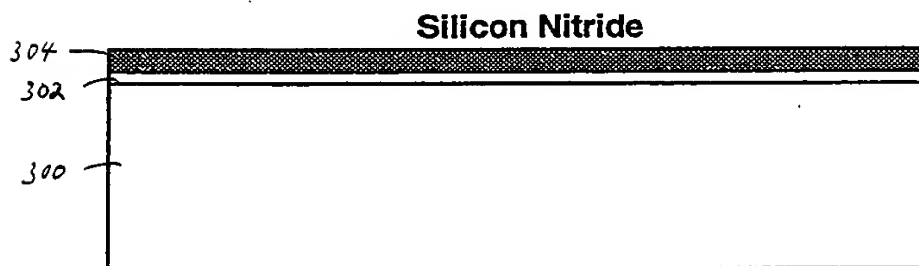


FIG. 8

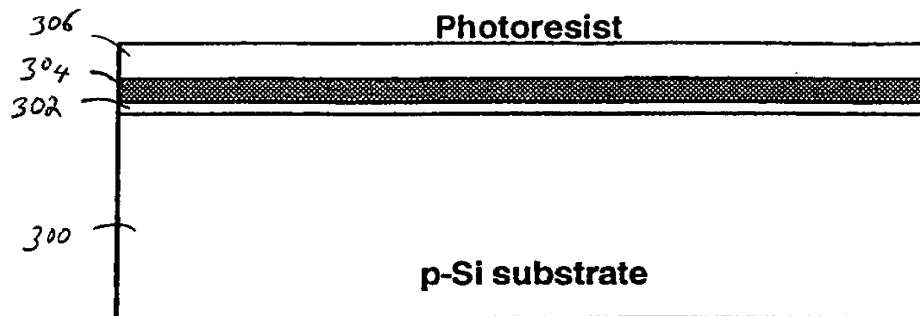


FIG. 9

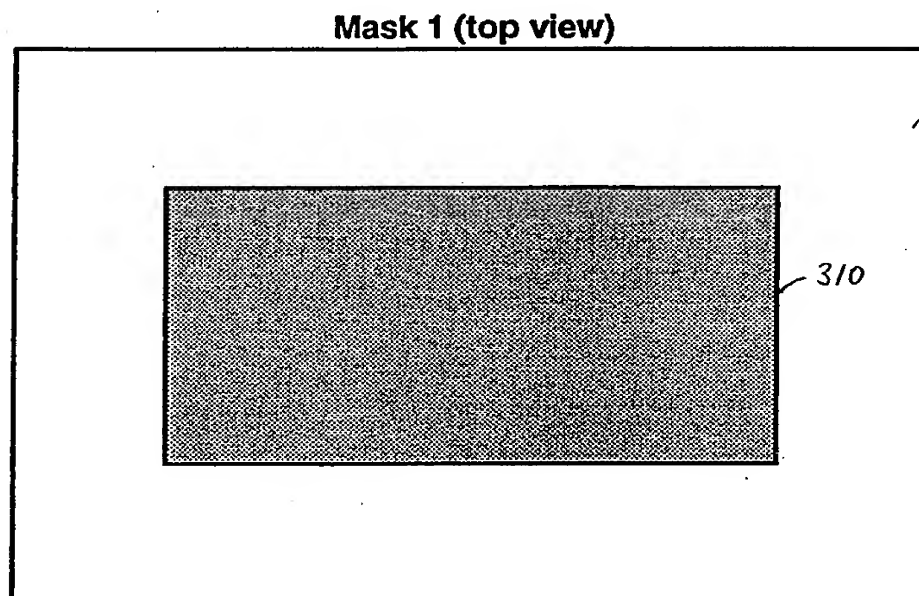


FIG. 10A

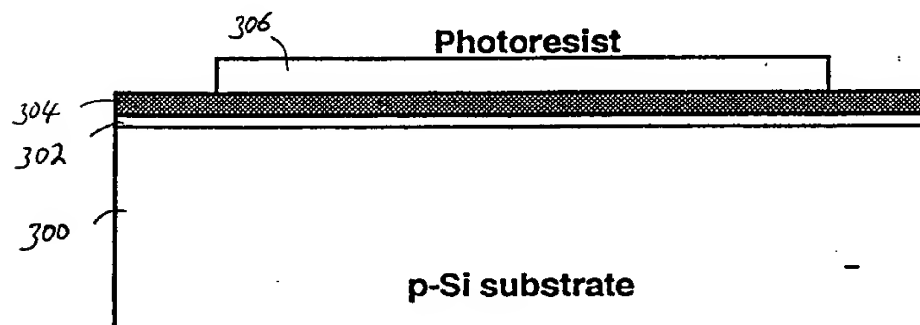
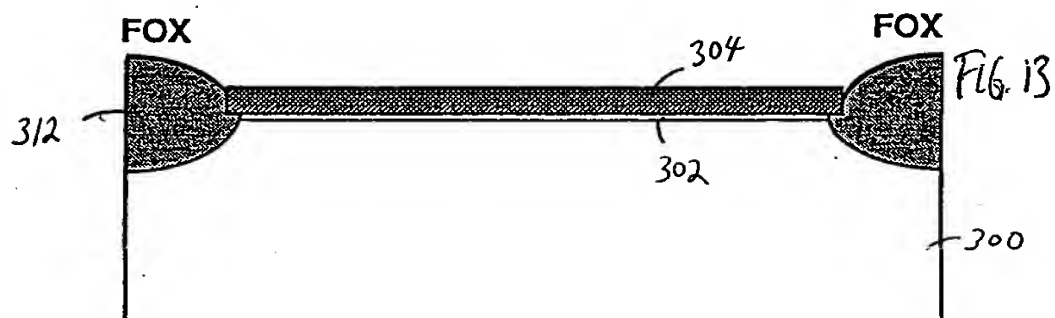
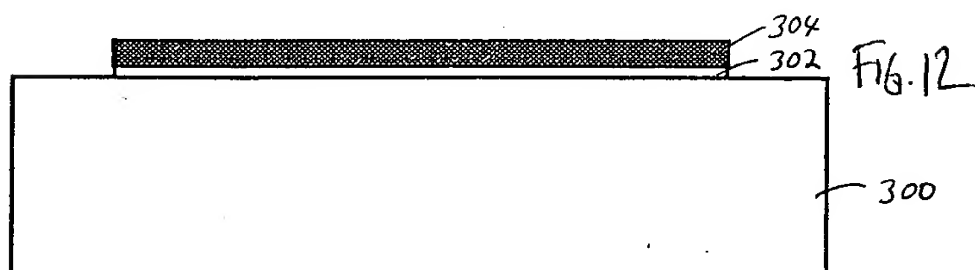
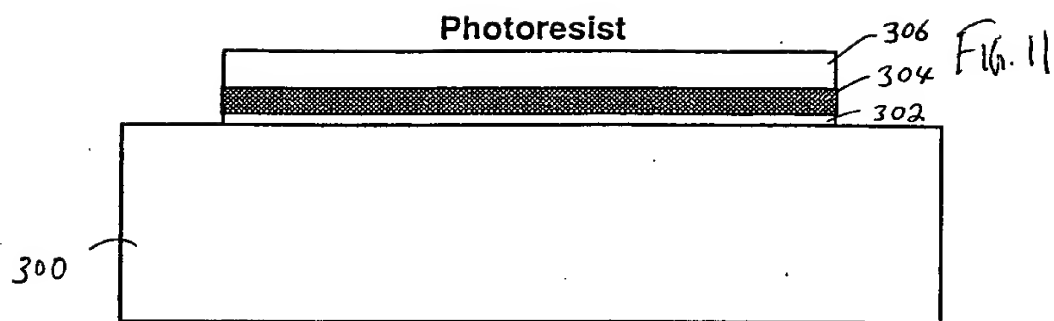
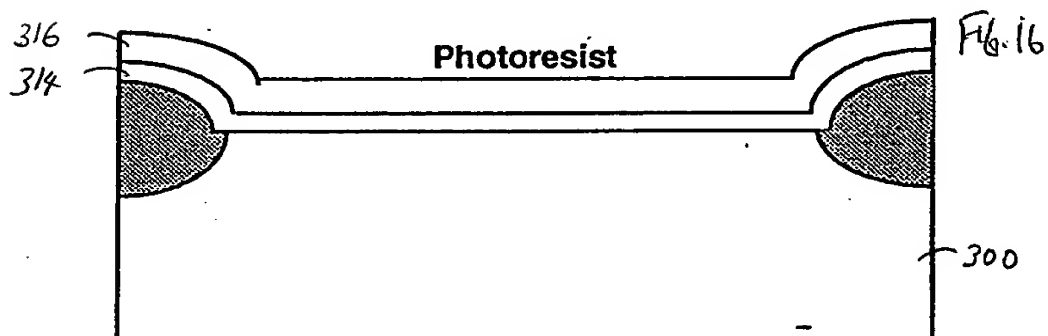
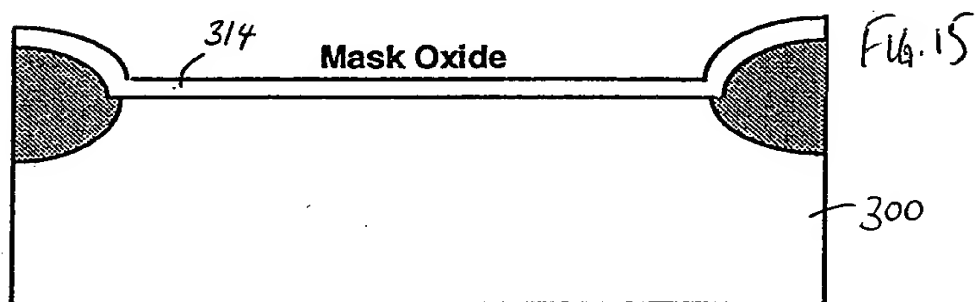
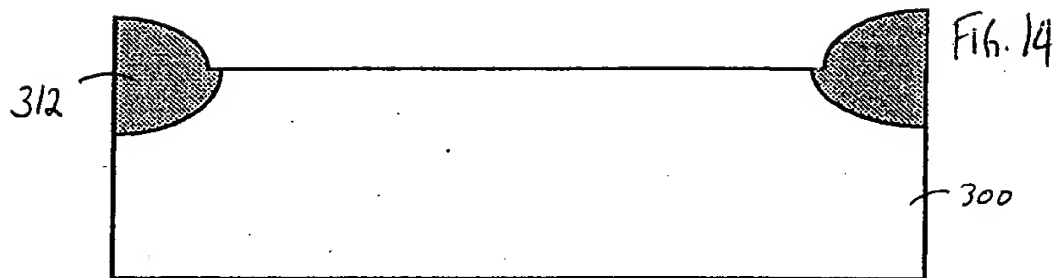
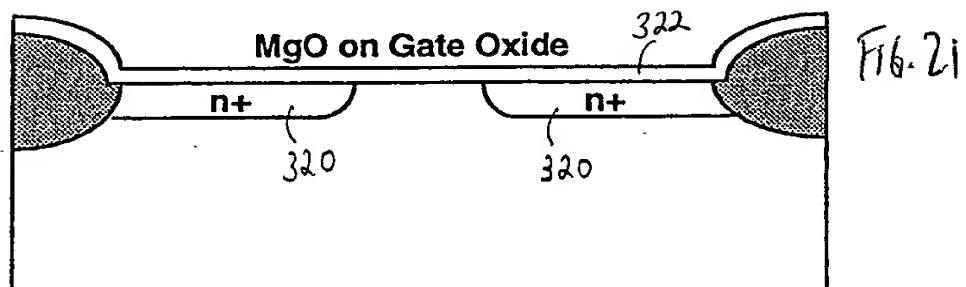
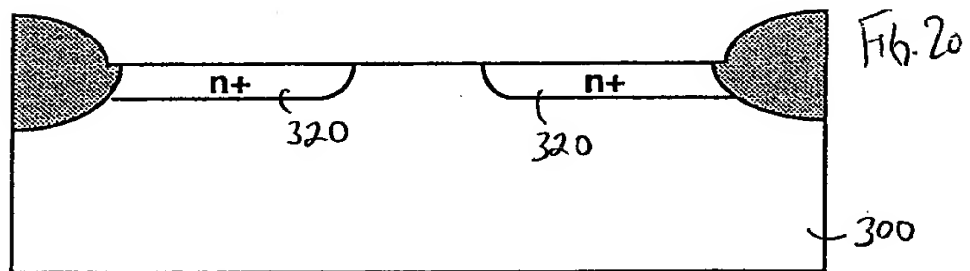
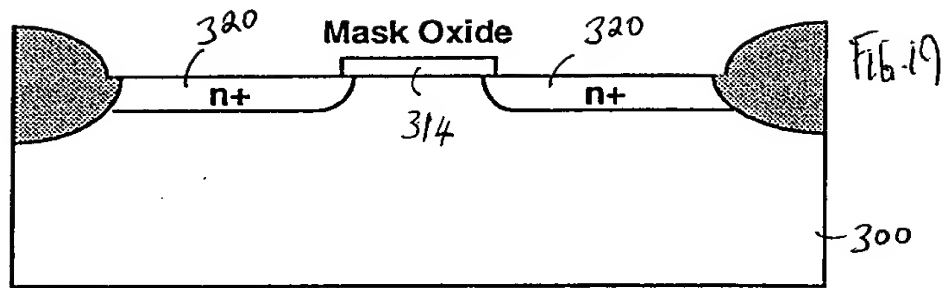


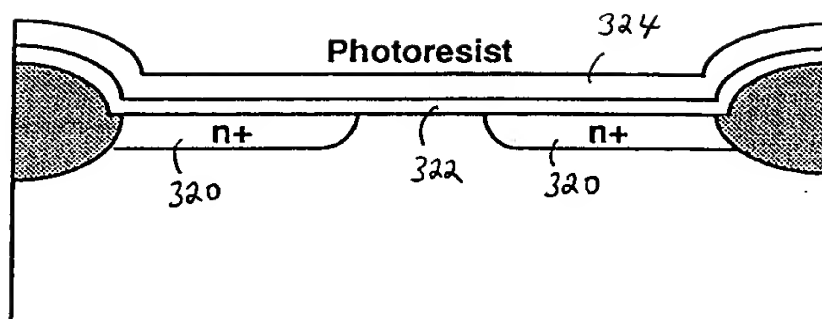
FIG. 10B





-300





Mask 3 (top view)

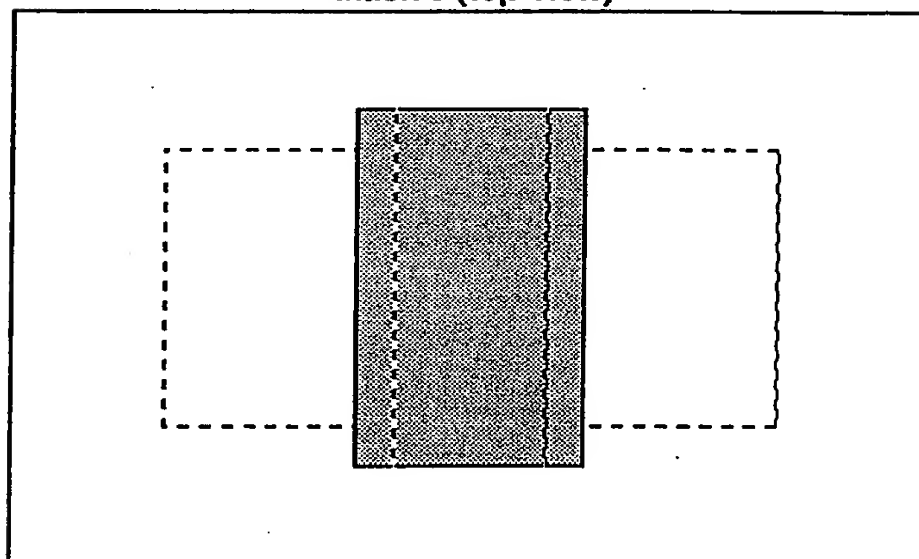
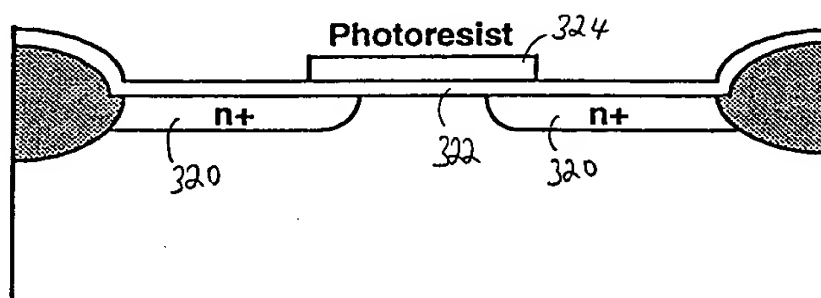


FIG. 23A



000001 04441400

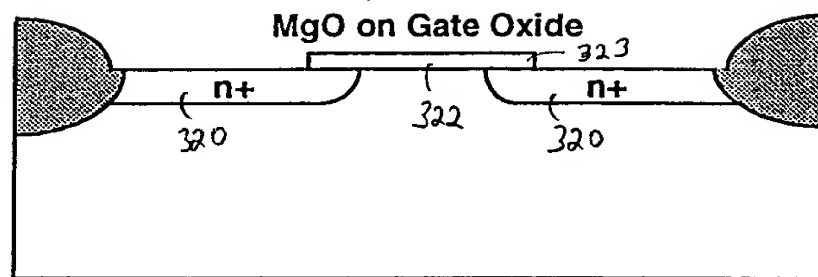


Fig. 24

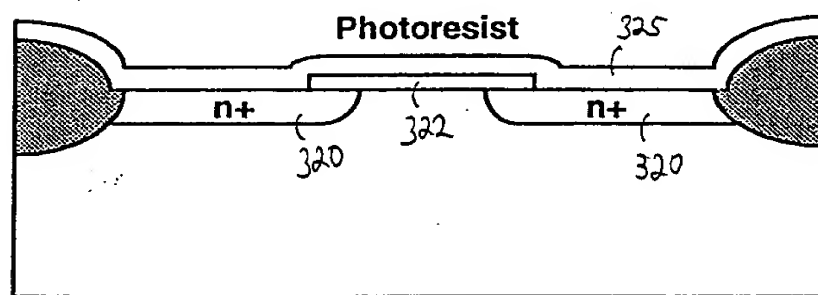


Fig. 25

Mask 4 (top view)

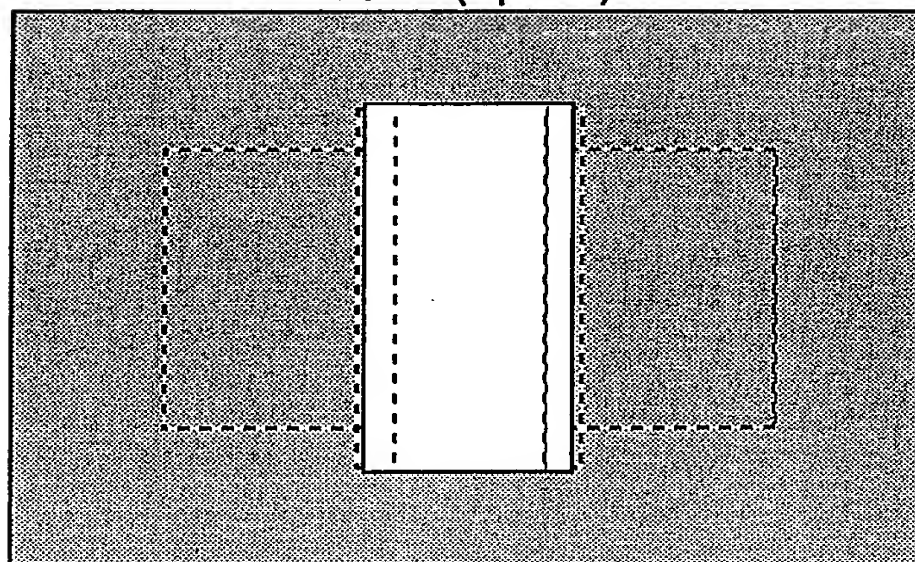
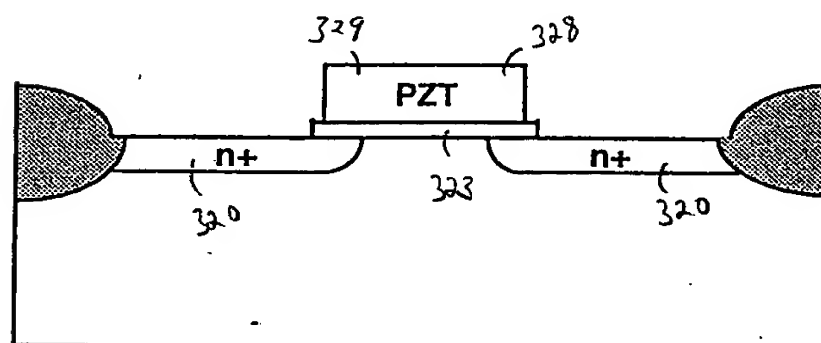
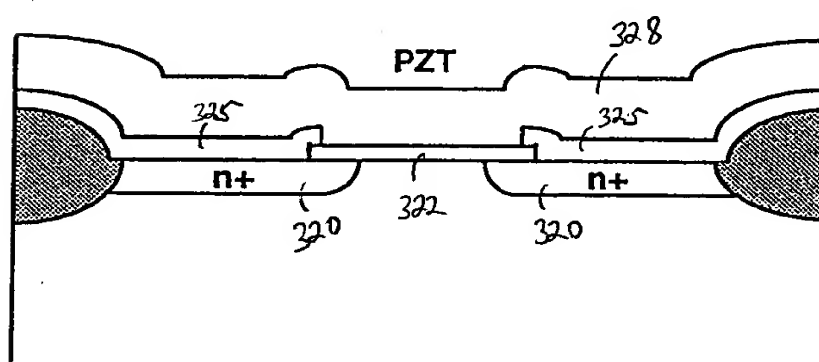
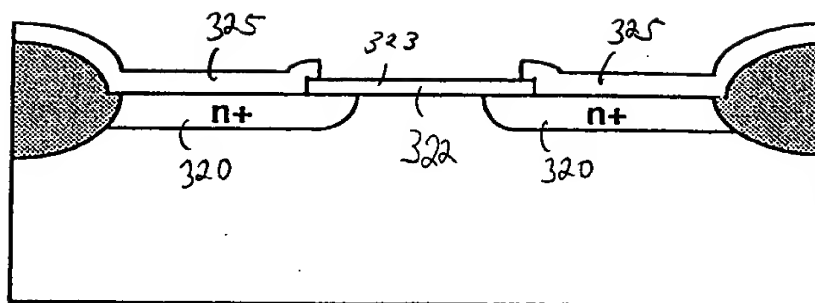
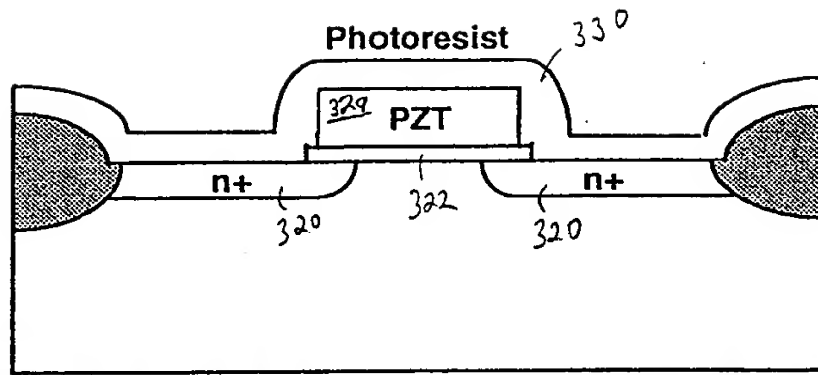


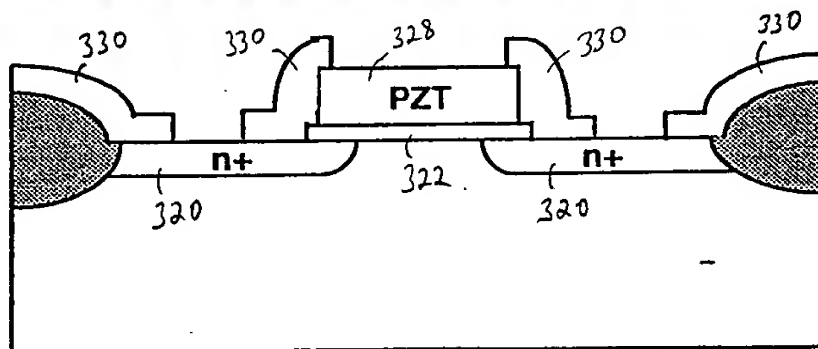
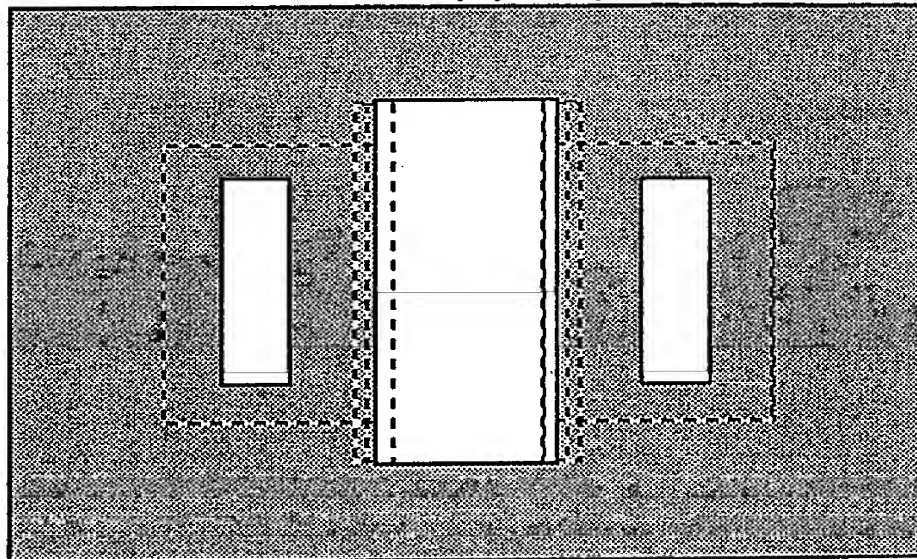
FIG. 26A

326





Mask 5 (top view)



334

PZT

n+

n+

A cross-sectional diagram of a device structure. At the base is a **p-Si substrate**. Above it is a layer of **MgO on Gate Oxide**. Two **n+** regions, labeled **336** and **340**, are formed in the gate oxide. A **PZT** layer, labeled **338**, is deposited on top of the MgO layer between the n+ regions. The structure is terminated on both sides by **FOX** (field oxide) regions.

Fib. 32

000001-000000

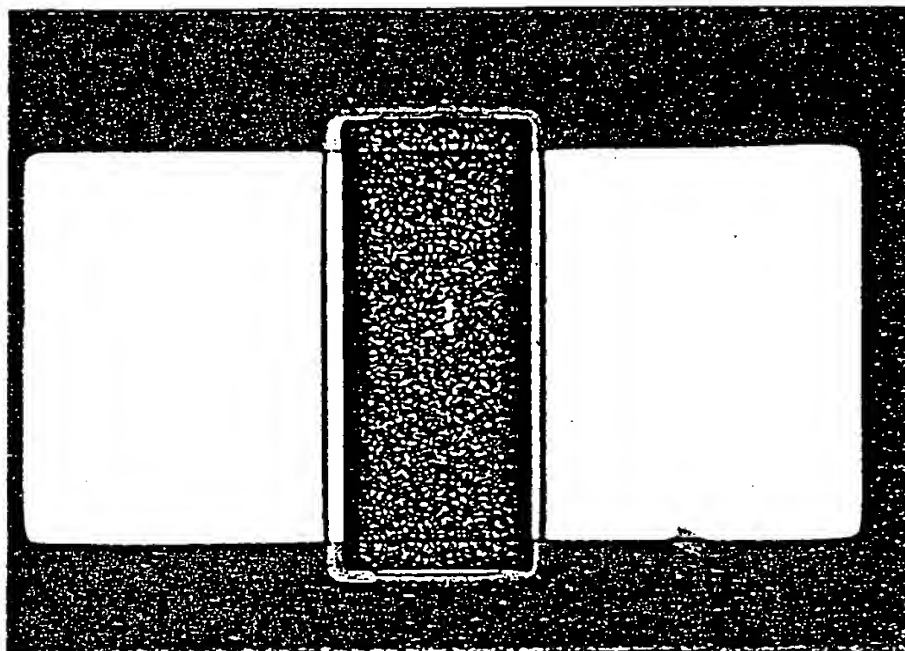


FIG. 33